Nava Setter

List of Publications by Year
in descending order

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195 papers	16,787 citations	10979 71 h-index	15249 126 g-index
198 all docs	198 docs citations	198 times ranked	9270 citing authors

#	Article	IF	Citations
1	Piezoelectric properties of Li- and Ta-modified (K0.5Na0.5)NbO3 ceramics. Applied Physics Letters, 2005, 87, 182905.	1.5	769
2	Dielectric and Structural Characteristics of Ba- and Sr-based Complex Perovskites as a Function of Tolerance Factor. Japanese Journal of Applied Physics, 1994, 33, 3984-3990.	0.8	627
3	Lead Free Piezoelectric Materials. Journal of Electroceramics, 2004, 13, 385-392.	0.8	603
4	Polarization fatigue in ferroelectric films: Basic experimental findings, phenomenological scenarios, and microscopic features. Journal of Applied Physics, 2001, 90, 1387-1402.	1.1	549
5	Non-Kolmogorov-Avrami switching kinetics in ferroelectric thin films. Physical Review B, 2002, 66, .	1.1	409
6	Effect of structural changes in complex perovskites on the temperature coefficient of the relative permittivity. Journal of Applied Physics, 1993, 74, 3414-3425.	1.1	397
7	Electroceramic materials. Acta Materialia, 2000, 48, 151-178.	3.8	377
8	{1 0 0}-Textured, piezoelectric Pb(Zrx, Ti1â^'x)O3 thin films for MEMS: integration, deposition and properties. Sensors and Actuators A: Physical, 2003, 105, 162-170.	2.0	375
9	Free-electron gas at charged domain walls in insulating BaTiO3. Nature Communications, 2013, 4, 1808.	5.8	367
10	Preparation and characterization of (K0.5Na0.5)NbO3 ceramics. Journal of the European Ceramic Society, 2006, 26, 861-866.	2.8	310
11	Orientation of rapid thermally annealed lead zirconate titanate thin films on (111) Pt substrates. Journal of Materials Research, 1994, 9, 2540-2553.	1.2	307
12	The spontaneous relaxorâ€ferroelectric transition of Pb(Sc0.5Ta0.5)O3. Journal of Applied Physics, 1993, 74, 5129-5134.	1.1	306
13	Principle of ferroelectric domain imaging using atomic force microscope. Journal of Applied Physics, 2001, 89, 1377-1386.	1.1	293
14	Microstructure, Electrical Conductivity, and Piezoelectric Properties of Bismuth Titanate. Journal of the American Ceramic Society, 1996, 79, 3124-3128.	1.9	290
15	Investigation of Pt/Ti bilayer metallization on silicon for ferroelectric thin film integration. Journal of Applied Physics, 1994, 75, 232-239.	1.1	267
16	Spontaneous (zeroâ€field) relaxorâ€“toâ€“ferroelectricâ€phase transition in disordered Pb(Sc1/2Nb1/2)O3. Journal of Applied Physics, 1995, 77, 1671-1676.	1.1	265
17	Electric-field-, temperature-, and stress-induced phase transitions in relaxor ferroelectric single crystals. Physical Review B, 2006, 73, .	1.1	265
18	Enhanced electromechanical response of ferroelectrics due to charged domain walls. Nature Communications, 2012, 3, 748.	5.8	265

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19	Piezoelectric micromachined ultrasonic transducers based on PZT thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2005, 52, 2276-2288.	1.7	262
20	Structural complexity of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:msub><mml:mrow><mml:mtext>Na</mml:mtext> Physical Review B, 2010, 82, .	1.1	262
21	Identification of passive layer in ferroelectric thin films from their switching parameters. Journal of Applied Physics, 1995, 78, 2623-2630.	1.1	235
22	Direct observation of region by region suppression of the switchable polarization (fatigue) in Pb(Zr,Ti)O3 thin film capacitors with Pt electrodes. Applied Physics Letters, 1998, 72, 2763-2765.	1.5	215
23	Ionic Polarizability of Conductive Metal Oxides and Critical Thickness for Ferroelectricity inBaTiO3. Physical Review Letters, 2006, 96, 107603.	2.9	215
24	Discrimination between bulk and interface scenarios for the suppression of the switchable polarization (fatigue) in Pb(Zr,Ti)O3 thin films capacitors with Pt electrodes. Applied Physics Letters, 1998, 72, 2478-2480.	1.5	209
25	Temperature stability of the piezoelectric properties of Li-modified KNN ceramics. Journal of the European Ceramic Society, 2007, 27, 4093-4097.	2.8	204
26	Rotator and extender ferroelectrics: Importance of the shear coefficient to the piezoelectric properties of domain-engineered crystals and ceramics. Journal of Applied Physics, 2007, 101, 054112.	1.1	203
27	Fabrication and characterization of PZT thin-film vibrators for micromotors. Sensors and Actuators A: Physical, 1995, 48, 157-165.	2.0	178
28	A study of the phase diagram of (K,Na,Li)NbO3 determined by dielectric and piezoelectric measurements, and Raman spectroscopy. Journal of Applied Physics, 2007, 102, .	1.1	175
29	Polarization charge as a reconfigurable quasi-dopant in ferroelectric thin films. Nature Nanotechnology, 2015, 10, 614-618.	15.6	170
30	Growth of Single-Crystalline KNbO3Nanostructures. Journal of Physical Chemistry B, 2006, 110, 58-61.	1.2	157
31	Ferroelectric-dielectric tunable composites. Journal of Applied Physics, 2006, 99, 074104.	1.1	157
32	Compositional Inhomogeneity in Liâ€•and Taâ€Modified (K, Na)NbO₃ Ceramics. Journal of the American Ceramic Society, 2007, 90, 3485-3489.	1.9	156
33	Dielectric spectroscopy of Ba(B1/2â€™B1/2â€˜)O3complex perovskite ceramics: Correlations between ionic parameters and microwave dielectric properties. I. Infrared reflectivity study (1012â€“1014Hz). Journal of Applied Physics, 1995, 77, 5341-5350.	1.1	155
34	Non-volatile ferroelectric control of ferromagnetism in (Ga,Mn)As. Nature Materials, 2008, 7, 464-467.	13.3	150
35	Piezoelectric anisotropyâ€“phase transition relations in perovskite single crystals. Journal of Applied Physics, 2003, 94, 6753-6761.	1.1	149
36	Use of Transmission Electron Microscopy for the Characterization of Rapid Thermally Annealed, Solution-Gel, Lead Zirconate Titanate Films. Journal of the American Ceramic Society, 1994, 77, 1209-1216.	1.9	147

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37	Controlling domain wall motion in ferroelectric thin films. Nature Nanotechnology, 2015, 10, 145-150.	15.6	135
38	Piezoelectric response and free-energy instability in the perovskite crystalsBaTiO3,PbTiO3, andPb(Zr,Ti)O3. Physical Review B, 2006, 73, .	1.1	131
39	Characterization of the effective electrostriction coefficients in ferroelectric thin films. Journal of Applied Physics, 2001, 89, 8066-8073.	1.1	130
40	Fatigue of piezoelectric properties in Pb(Zr,Ti)O3 films. Applied Physics Letters, 1996, 68, 2577-2579.	1.5	123
41	Preisach modeling of piezoelectric nonlinearity in ferroelectric ceramics. Journal of Applied Physics, 2001, 89, 5067-5074.	1.1	121
42	Preparation and Characterization of KNbO3 Ceramics. Journal of the American Ceramic Society, 2005, 88, 1754-1759.	1.9	120
43	Removal of 90Â° domain pinning in (100)â€‰Pb(Zr0.15Ti0.85)O3 thin films by pulsed operation. Applied Physics Letters, 1998, 72, 3217-3219.	1.5	119
44	Ferroelectric translational antiphase boundaries in nonpolar materials. Nature Communications, 2014, 5, 3031.	5.8	119
45	Design of novel thin-film piezoelectric accelerometer. Sensors and Actuators A: Physical, 1996, 56, 239-249.	2.0	118
46	Bâ€site order and infrared reflectivity inA(Bâ€™Bâ€˜)O3complex perovskite ceramics. Journal of Applied Physics, 1994, 76, 2086-2092.	1.1	114
47	Highâ€Temperature Instability of Liâ€•and Taâ€Modified (K,Na)NbO₃ Piezoceramics. Journal of the American Ceramic Society, 2008, 91, 1962-1970.	1.9	112
48	Effect of Nb Doping on the Microstructure of Sol-Gel-Derived PZT Thin Films. Journal of the American Ceramic Society, 1995, 78, 1513-1520.	1.9	109
49	Dielectric spectroscopy of Ba(B1/2â€™B1/2â€˜)O3complex perovskite ceramics: Correlations between ionic parameters and microwave dielectric properties. II. Studies below the phonon eigenfrequencies (102â€“1012Hz). Journal of Applied Physics, 1995, 77, 5351-5364.	1.1	106
50	Piezoelectric Response and Polarization Switching in Small Anisotropic Perovskite Particles. Nano Letters, 2004, 4, 1339-1342.	4.5	106
51	Monodomain versus polydomain piezoelectric response of 0.67Pb(Mg1/3Nb2/3)O3â€“0.33PbTiO3 single crystals along nonpolar directions. Applied Physics Letters, 2003, 83, 527-529.	1.5	103
52	Investigation of relaxors that transform spontaneously into ferroelectrics. Ferroelectrics, 1994, 151, 343-348.	0.3	101
53	Defect ordering and defectâ€“domain-wall interactions in PbTiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>: A first-principles study. Physical Review B, 2013, 88, .	1.1	100
54	Landau thermodynamic potential for BaTiO3. Journal of Applied Physics, 2007, 101, 104115.	1.1	99

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55	Domain engineering of the transverse piezoelectric coefficient in perovskite ferroelectrics. Journal of Applied Physics, 2005, 98, 014102.	1.1	97
56	Raman spectroscopy of (K,Na)NbO3 and (K,Na)1â^'xLixNbO3. Applied Physics Letters, 2008, 93, .	1.5	97
57	Crystal orientation dependence of the piezoelectric d33 coefficient in tetragonal BaTiO3 as a function of temperature. Applied Physics Letters, 2002, 80, 652-654.	1.5	96
58	Electroceramics: looking ahead. Journal of the European Ceramic Society, 2001, 21, 1279-1293.	2.8	94
59	Ferroelectricity in Asymmetric Metal-Ferroelectric-Metal Heterostructures: A Combined First-Principlesâ€"Phenomenological Approach. Physical Review Letters, 2007, 98, 207601.	2.9	93
60	Soft and central mode behaviour in PbMg1/3Nb2/3O3relaxor ferroelectric. Journal of Physics Condensed Matter, 2005, 17, 3965-3974.	0.7	91
61	Broad-band dielectric response of PbMg1/3Nb2/3O3 relaxor ferroelectrics: Single crystals, ceramics and thin films. Journal of the European Ceramic Society, 2006, 26, 2867-2875.	2.8	91
62	Microfabricated Lamb wave device based on PZT sol-gel thin film for mechanical transport of solid particles and liquids. Journal of Microelectromechanical Systems, 1997, 6, 337-346.	1.7	89
63	Built-in electric field assisted nucleation and coercive fields in ferroelectric thin films. Integrated Ferroelectrics, 1994, 4, 1-12.	0.3	87
64	Surface-Stimulated Nucleation of Reverse Domains in Ferroelectrics. Physical Review Letters, 2005, 94, 107602.	2.9	83
65	Formation of charged ferroelectric domain walls with controlled periodicity. Scientific Reports, 2015, 5, 15819.	1.6	83
66	Negative-pressure-induced enhancement in a freestanding ferroelectric. Nature Materials, 2015, 14, 985-990.	13.3	82
67	Role of Defects in the Ferroelectric Relaxor Lead Scandium Tantalate. Journal of the American Ceramic Society, 1995, 78, 1947-1952.	1.9	80
68	Nature of nonlinear imprint in ferroelectric films and long-term prediction of polarization loss in ferroelectric memories. Journal of Applied Physics, 2004, 96, 6616-6623.	1.1	80
69	Quantitative analysis of the bit size dependence on the pulse width and pulse voltage in ferroelectric memory devices using atomic force microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 818.	1.6	77
70	Temperature dependence of the direct piezoelectric effect in relaxor-ferroelectric single crystals: Intrinsic and extrinsic contributions. Journal of Applied Physics, 2006, 100, 084103.	1.1	77
71	Controlled stripes of ultrafine ferroelectric domains. Nature Communications, 2014, 5, 4677.	5.8	77
72	Electromechanicalâ€‰propertiesâ€‰andâ€‰self-polarizationâ€‰inâ€‰relaxor Pb(Mg1/3Nb2/3)O3 thin films. Journal of Applied Physics, 2001, 89, 1393-1401.	1.1	73

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73	Enhancement of the piezoelectric response of tetragonal perovskite single crystals by uniaxial stress applied along the polar axis: A free-energy approach. Physical Review B, 2005, 72, .	1.1	71
74	Bent Ferroelectric Domain Walls as Reconfigurable Metallic-Like Channels. Nano Letters, 2015, 15, 8049-8055.	4.5	68
75	High figure-of-merit porous Pb1â^'xCaxTiO3 thin films for pyroelectric applications. Applied Physics Letters, 1998, 72, 2409-2411.	1.5	65
76	Influence of flexoelectric coupling on domain patterns in ferroelectrics. Physical Review B, 2014, 89, .	1.1	62
77	The nonlinearity and subswitching hysteresis in hard and soft PZT. Journal of the European Ceramic Society, 2005, 25, 2483-2486.	2.8	61
78	Ferroelectric gate for control of transport properties of two-dimensional electron gas at AlGaNâ^•GaN heterostructures. Applied Physics Letters, 2006, 88, 043512.	1.5	59
79	Processing and Properties of Screenâ€Printed Lead Zirconate Titanate Piezoelectric Thick Films on Electroded Silicon. Journal of the American Ceramic Society, 2001, 84, 2863-2868.	1.9	58
80	Dielectric and electromechanical properties of ferroelectric-relaxor 0.9 Pb(Mg1/3Nb2/3)O3â€“0.1PbTiO3 thin films. Journal of Applied Physics, 2001, 90, 4682-4689.	1.1	56
81	Properties of ferroelectric PbTiO3 thin films. Journal of Applied Physics, 2002, 91, 1495-1501.	1.1	56
82	Tuning of direct current bias-induced resonances in micromachined Ba0.3Sr0.7TiO3 thin-film capacitors. Journal of Applied Physics, 2007, 102, .	1.1	55
83	NÃ©el-like domain walls in ferroelectric Pb(Zr,Ti)O3 single crystals. Nature Communications, 2016, 7, 12385.	5.8	55
84	Thermally Induced Cooperative Molecular Reorientation and Nanoscale Polarization Switching Behaviors of Ultrathin Poly(vinylidene fluoride-trifluoroethylene) Films. Journal of Physical Chemistry B, 2011, 115, 13455-13466.	1.2	54
85	Long-term retention in organic ferroelectric-graphene memories. Applied Physics Letters, 2012, 100, 023507.	1.5	54
86	Direct piezoelectric effect in relaxor-ferroelectric single crystals. Journal of Applied Physics, 2004, 95, 5679-5684.	1.1	52
87	Ferroelectric properties of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method below the Curie temperature. Applied Physics Letters, 2004, 84, 5094-5096.	1.5	52
88	Unusual size effect on the polarization patterns in micron-size Pb(Zr,Ti)O3 film capacitors. Applied Physics Letters, 2002, 80, 4804-4806.	1.5	50
89	Pyroelectric properties of (1â^'x)Pb(Mg1â^•3Nb2â^•3)O3-xPbTiO3 and (1â^'x)Pb(Zn1â^•3Nb2â^•3)O3-xPbTiO3 single crystals measured using a dynamic method. Journal of Applied Physics, 2004, 96, 2811-2815.	1.1	49
90	Microscopic aspects of the region-by-region polarization reversal kinetics of polycrystalline ferroelectric Pb(Zr,Ti)O3 films. Applied Physics Letters, 2005, 86, 012902.	1.5	47

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91	Epitaxialâˆ•amorphous Ba0.3Sr0.7TiO3 film composite structure for tunable applications. Applied Physics Letters, 2006, 89, 032905.	1.5	45
92	Tunable thin film bulk acoustic wave resonator based on Ba_xSr_{1-x}TiO₃ thin film. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2010, 57, 379-385.	1.7	45
93	Strain relaxation of epitaxial SrTiO3 thin films on LaAlO3 by two-step growth technique. Applied Physics Letters, 2005, 86, 142904.	1.5	43
94	Large and stable thickness coupling coefficients of [001]C-oriented KNbO3 and Li-modified (K,Na)NbO3 single crystals. Applied Physics Letters, 2007, 90, 062904.	1.5	43
95	Restricted domain growth and polarization reversal kinetics in ferroelectric polymer thin films. Journal of Applied Physics, 2008, 103, 084120.	1.1	43
96	Piezoelectric enhancement under negative pressure. Nature Communications, 2016, 7, 12136.	5.8	39
97	Piezoelectricity and Phase Transitions of the Mixed-Layer Bismuth Titanate Niobate Bi7Ti4NbO21. Journal of the American Ceramic Society, 1995, 78, 3142-3144.	1.9	38
98	Use of Ferroelectric Hysteresis Parameters for Evaluation of Niobium Effects in Lead Zirconate Titanate Thin Films. Journal of the American Ceramic Society, 1997, 80, 336-342.	1.9	38
99	Lead loss, preferred orientation, and the dielectric properties of solâ€gel prepared lead titanate thin films. Applied Physics Letters, 1994, 65, 2678-2680.	1.5	37
100	Model of a low-permittivity and high-tunability ferroelectric based composite. Applied Physics Letters, 2007, 90, 162901.	1.5	36
101	Electrical tuning of dc bias induced acoustic resonances in paraelectric thin films. Journal of Applied Physics, 2008, 104, .	1.1	36
102	Relationship between nanostructure and dielectric response of lead scandium tantalate â€" (I) structure and domain textures. Physica B: Condensed Matter, 1995, 205, 305-326.	1.3	35
103	Large enhancement of the piezoelectric response in perovskite crystals by electric bias field antiparallel to polarization. Applied Physics Letters, 2004, 85, 2890-2892.	1.5	34
104	Three-dimensional ferroelectric domain imaging of bulk Pb(Zr,Ti)O3 by atomic force microscopy. Applied Physics Letters, 2004, 84, 2382-2384.	1.5	34
105	Ferroelectric property of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method. Journal of Materials Research, 2004, 19, 1862-1868.	1.2	32
106	Aluminate sodalite Sr8[Al12O24](CrO4)2-a new ferroelectric material. Ferroelectrics, 1984, 56, 49-52.	0.3	31
107	Evidence for forward domain growth being rate-limiting step in polarization switching in â€˜111â€‰-oriented-Pb(Zr0.45Ti0.55)O3 thin-film capacitors. Applied Physics Letters, 2002, 81, 3437-3439.	1.5	31
108	Electric-field-induced orthorhombic to rhombohedral phase transition in [111]C-oriented 0.92Pb(Zn1â…“Nb2â…“)O3â€“0.08PbTiO3. Journal of Applied Physics, 2005, 97, 064101.	1.1	31

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109	Microstructural evolution of dense and porous pyroelectric Pb_{1â^'x}Ca_xTiO₃ thin films. Journal of Materials Research, 1999, 14, 2012-2022.	1.2	30
110	Ferroelectric and piezoelectric properties of lanthanoid-substituted Bi4Ti3O12 thin films grown on (111)Pt and (100)IrO2 electrodes. Applied Physics Letters, 2005, 86, 172904.	1.5	29
111	Selfâ€Assembled Perovskiteâ€Fluorite Oblique Nanostructures for Adaptive (Tunable) Electronics. Advanced Materials, 2009, 21, 1363-1367.	11.1	29
112	Large-scale fabrication of titanium-rich perovskite PZT submicro/nano wires and their electromechanical properties. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2009, 56, 1813-1819.	1.7	29
113	Size effect in ferroelectrics: Competition between geometrical and crystalline symmetries. Physical Review B, 2011, 83, .	1.1	27
114	Mechanism of hydrothermal growth of ferroelectric PZT nanowires. Journal of Crystal Growth, 2012, 347, 1-6.	0.7	27
115	Controlled Charging of Ferroelastic Domain Walls in Oxide Ferroelectrics. ACS Applied Materials & Interfaces, 2017, 9, 6539-6546.	4.0	27
116	Excess lead in the perovskite lattice of pzt thin films made by in-situ reactive sputtering. Integrated Ferroelectrics, 2001, 36, 53-62.	0.3	25
117	Processing and dielectric characterization of Ba0.3Sr0.7TiO3 thin films on alumina substrates. Journal of the European Ceramic Society, 2007, 27, 2945-2948.	2.8	25
118	Polarity of translation boundaries in antiferroelectric PbZrO3. Materials Research Bulletin, 2015, 62, 101-105.	2.7	25
119	The role of some cage ion substitutions for the phase transition characteristics of aluminate sodalites. Ferroelectrics, 1984, 56, 45-48.	0.3	24
120	Structural and dielectric properties of strain-controlled epitaxial SrTiO3 thin films by two-step growth technique. Journal of Applied Physics, 2005, 98, 054105.	1.1	24
121	Epitaxial growth of (SrBa)Nb2O6 thin films on SrTiO3 single crystal substrate. Journal of Applied Physics, 2006, 100, 104110.	1.1	24
122	Ferroelectric transistors with improved characteristics at high temperature. Applied Physics Letters, 2010, 97, .	1.5	24
123	Dielectric Properties of Complex Perovskite Lead Scandium Tantalate under dc Bias. Journal of the American Ceramic Society, 1998, 81, 1577-1582.	1.9	23
124	Epitaxial growth of Ba0.3Sr0.7TiO3 thin films on Al2O3(0001) using ultrathin TiN layer as a sacrificial template. Applied Physics Letters, 2007, 90, 142911.	1.5	23
125	What is a ferroelectricâ€“a materials designer perspective. Ferroelectrics, 2016, 500, 164-182.	0.3	23
126	Solid Solutions of Lead Metaniobateâ€”Stabilization of the Ferroelectric Polymorph and the Effect on the Lattice Parameters, Dielectric, Ferroelectric, and Piezoelectric Properties. Journal of the American Ceramic Society, 2014, 97, 220-227.	1.9	22

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127	Preferential Creation of Polar Translational Boundaries by Interface Engineering in Antiferroelectric PbZrO₃ Thin Films. Advanced Materials Interfaces, 2015, 2, 1500349.	1.9	22
128	Asymmetric structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mn>90</mml:mn><mml:mo>â˜</mml:mo></mml:msup></m walls and interactions with defects in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>PbTiO</mml:mi><mml:mn>3</mml:mn></mml:msub></m Physical Review B, 2016, 93, .	1.1	22
129	Uniaxial-stress induced phase transitions in [001]C-poled 0.955Pb(Zn1âˆ•3Nb2âˆ•3)O3â€“0.045PbTiO3. Applied Physics Letters, 2007, 90, 152907.	1.5	21
130	Nanoscale Defect Engineering and the Resulting Effects on Domain Wall Dynamics in Ferroelectric Thin Films. Advanced Functional Materials, 2017, 27, 1605196.	7.8	21
131	Freeâ€Carrierâ€Compensated Charged Domain Walls Produced with Superâ€Bandgap Illumination in Insulating Ferroelectrics. Advanced Materials, 2016, 28, 9498-9503.	11.1	20
132	Evidence for dielectric aging due to progressive<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>180</mml:mn><mml:mo>Â°</mml:mo></mml:mrow></mml:math>domain wall pinning in polydomain<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"		

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145	Annealing effect on dislocations in SrTiO3â^•LaAlO3 heterostructures. Journal of Applied Physics, 2007, 101, 064102.	1.1	14
146	Structure and pressure-induced ferroelectric phase transition in antiphase domain boundaries of strontium titanate from first principles. Physical Review B, 2016, 94, .	1.1	14
147	Charge screening strategy for domain pattern control in nano-scale ferroelectric systems. Scientific Reports, 2017, 7, 5236.	1.6	14
148	Flexible polarization rotation at the ferroelectric/metal interface as a seed for domain nucleation. Physical Review B, 2018, 98, .	1.1	14
149	Growth-mode induced defects in epitaxial SrTiO₃ thin films grown on single crystal LaAlO₃ by a two-step PLD process. Journal of Materials Research, 2011, 26, 770-774.	1.2	13
150	Correlation between dielectric anisotropy and positive or zero transverse piezoelectric coefficients in perovskite ferroelectric single crystals. Applied Physics Letters, 2005, 87, 102904.	1.5	12
151	Nonvolatile Gate Effect in a Ferroelectric-Semiconductor Quantum Well. Physical Review Letters, 2006, 97, 247601.	2.9	11
152	Extension of the dielectric tunability range in ferroelectric materials by electric bias field antiparallel to polarization. Applied Physics Letters, 2006, 88, 082903.	1.5	11
153	Room temperature concurrent formation of ultra-dense arrays of ferroelectric domain walls. Applied Physics Letters, 2015, 107, .	1.5	10
154	Low voltage Ferroelectric FET with sub-100nm copolymer P(VDF-TrFE) gate dielectric for non-volatile 1T memory. , 2008, , .		9
155	Moving antiphase boundaries using an external electric field. Applied Physics Letters, 2015, 107, .	1.5	9
156	Effect of Nb doping on the hysteresis parameters of sol-gel derived thin films. Microelectronic Engineering, 1995, 29, 271-274.	1.1	7
157	Sol-gel processing of pnzst thin films on and metallizations. Journal of the European Ceramic Society, 1997, 17, 1231-1238.	2.8	7
158	Insights in the solâ€“gel processing of Pb(Mg1/3Nb2/3)O3. The synthesis and crown structure of a new lead magnesium cluster: Pb6Mg12(Î¼-OAc)6(Î¼2,Î·2-OAc)18(Î¼3,Î·2-OC2H4OPri)12. Inorganic Chemistry Communication, 2002, 5, 316-318.	1.8	6
159	Microwave phase shifters based on sol-gel derived Ba<inf>0</inf>.<inf>3</inf>Sr<inf>0</inf>.<inf>7</inf>TiO<inf>3</inf> ferroelectric thin films. , 2007, , .		6
160	Nonvolatile gate effect in the PZT/AlGaN/GaN heterostructure. Journal of the European Ceramic Society, 2007, 27, 4307-4311.	2.8	6
161	Effect of dopants on the crystallization mechanism of PZT thin films. Ferroelectrics, 1999, 225, 327-334.	0.3	5
162	Analytical modeling of the apparent d/sub 33/ piezoelectric coefficient determined by the direct quasistatic method for different boundary conditions. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2005, 52, 1897-1903.	1.7	5

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163	Transmission-electron-microscopy study of quasi-epitaxial tungsten-bronze (Sr2.5Ba2.5Nb10O30) thin film on perovskite (SrTiO3) single crystal. Journal of Materials Research, 2007, 22, 157-163.	1.2	5
164	Qualitative distinction in enhancement of the piezoelectric response in PbTiO3 in proximity of coercive fields: 90Â° versus 180Â° switching. Journal of Applied Physics, 2007, 101, 104119.	1.1	5
165	Growth process approaches for improved properties of tunable ferroelectric thin films. Journal of the European Ceramic Society, 2007, 27, 3753-3758.	2.8	5
166	Preparation and electromechanical properties of Pb(Mg1/3Nb2/3)O3thin film. Ferroelectrics, 1999, 224, 291-298.	0.3	4
167	Sol-Gel Derived Pb(Sc0.5Nb0.5)O3Thin Films: Processing and Dielctric Properties. Japanese Journal of Applied Physics, 2002, 41, 6765-6767.	0.8	4
168	Preface to Special Topic: Invited Papers from the International Symposium on Piezoresponse Force Microscopy and Nanoscale Phenomena in Polar Materials, Aveiro, Portugal, 2009. Journal of Applied Physics, 2010, 108, 041901.	1.1	4
169	Materials and Devices for Nanoelectronic Systems Beyond Ultimately Scaled CMOS. , 2009, , 23-44.		4
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